Unit in mm

TOSHIBA Photocoupler GaAs IRed & Photo-Transistor

# **TLP631,TLP632**

# Programmable Controllers AC / DC-Input Module Solid State Relay

The TOSHIBA TLP631 and TLP632 consist of a photo–transistor optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP.

TLP632 is no-base internal connection for high-EMI environments.

- Collector-emitter voltage: 55 V (min.)
- Current transfer ratio: 50% (min.)

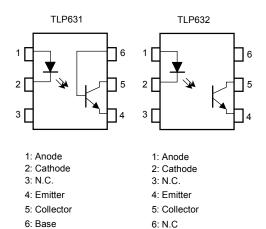
Rank GB: 100% (min.)

- Isolation voltage: 5000V<sub>rms</sub> (min.)
- UL recognized: UL1577, file no. E67349

# 7.12±0.25 9.5 0.5±0.1 1.2±0.15 28 0.25±0.05 7.85 ~ 8.80 11-7A8

Weight: 0.4 g

#### Pin Configurations (top view)





#### Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit	
	Forward current	IF	60	mA	
	Forward current derating (Ta ≥ 39°C)	ΔI <sub>F</sub> / °C	-0.7	mA / °C	
ЕÐ	Peak forward current (100µs pulse, 100pps)	I <sub>FP</sub>	1	Α	
	Reverse voltage	V <sub>R</sub>	5	V	
	Junction temperature	Tj	125	°C	
	Collector-emitter voltage	V <sub>CEO</sub>	55	V	
	Collector-base voltage (TLP631)	V <sub>CBO</sub>	80	V	
	Emitter-collector voltage	V <sub>ECO</sub>	7	V	
ctor	Emitter–base voltage (TLP631)	V <sub>EBO</sub>	7	V	
Detector	Collector current	I <sub>C</sub>	50	mA	
	Power dissipation	PC	150	mW	
	Power dissipation derating (Ta ≥ 25°C)	ΔP <sub>C</sub> / °C	-1.5	mW / °C	
	Junction temperature	Tj	125	°C	
Sto	rage temperature range	T <sub>stg</sub>	-55~125	°C	
Оре	erating temperature range	T <sub>opr</sub>	-55~100	°C	
Lead soldering temperature (10s)		T <sub>sol</sub>	260	°C	
Total package power dissipation		P <sub>T</sub>	250	mW	
Tota	al package power dissipation derating (Ta≥ 25°C)	ΔP <sub>T</sub> / °C	-2.5	mW / °C	
Isol	ation voltage (AC, 1 min., R.H. ≤ 60%)	BVS	5000	V <sub>rms</sub>	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Recommended Operating Conditions**

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V <sub>CC</sub>	_	5	24	V
Forward current	lF	_	16	25	mA
Collector current	IC	_	1	10	mA
Operating temperature	T <sub>opr</sub>	-25	_	85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.



## Individual Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
	Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 10 mA	1.0	1.15	1.3	V
LED	Reverse current	I <sub>R</sub>	V <sub>R</sub> = 5V	_	_	10	μΑ
	Capacitance	C <sub>T</sub>	V = 0, f = 1 MHz	_	30	-	pF
	Collector–emitter breakdown voltage	V <sub>(BR)</sub> CEO	I <sub>C</sub> = 0.5 mA	55	_	_	V
Detector	Emitter–collector breakdown voltage	V <sub>(BR)</sub> ECO	I <sub>E</sub> = 0.1 mA	7	_	_	V
	Collector-base breakdown voltage (TLP631)	V <sub>(BR)</sub> CBO	I <sub>C</sub> = 0.1 mA	80	_	ı	V
	Emitter-base breakdown voltage (TLP631)	V <sub>(BR)</sub> EBO	I <sub>E</sub> = 0.1 mA	7	_	_	V
	Callactor dark current	Collector dark current ICEO	V <sub>CE</sub> = 24 V	_	10	100	nA
	Collector dark current		V <sub>CE</sub> = 24 V, Ta = 85°C	_	2	50	μA
	Capacitance collector to emitter	C <sub>CE</sub>	V = 0, f = 1 MHz	_	10	_	pF

## **Coupled Electrical Characteristics (Ta = 25°C)**

Characteristic	Symbol	Test Condition	MIn.	Тур.	Max.	Unit
Current transfer ratio	I <sub>C</sub> / I <sub>F</sub>	I <sub>F</sub> = 5 mA, V <sub>CE</sub> = 5 V Rank GB	50	-	600	- %
			100	1	600	
Saturated CTR	I <sub>C</sub> / I <sub>F (sat)</sub>	$I_F$ = 1 mA, $V_{CE}$ = 0.4 V Rank GB	_	60	_	%
			30	_	_	/0
Collector–emitter saturation voltage	V <sub>CE (sat)</sub>	I <sub>C</sub> = 2.4 mA, I <sub>F</sub> = 8 mA	_		0.4	V



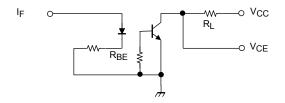
# Isolation Characteristics (Ta = 25°C)

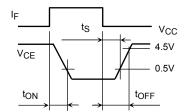
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance (input to output)	Cs	V <sub>S</sub> = 0, f = 1 MHz	_	0.8	_	pF
Isolation resistance	R <sub>S</sub>	V <sub>S</sub> = 500 V, R.H. ≤ 60%	5×10 <sup>10</sup>	10 <sup>14</sup>	_	Ω
	BVS	AC, 1 minute	5000	_	_	V
Isolation voltage		AC, 1 second, in oil	_	10000	_	V <sub>rms</sub>
		DC, 1 minute, in oil	_	10000	_	V <sub>dc</sub>

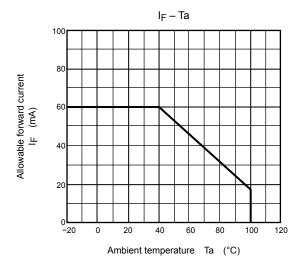
### **Switching Characteristics (Ta = 25°C)**

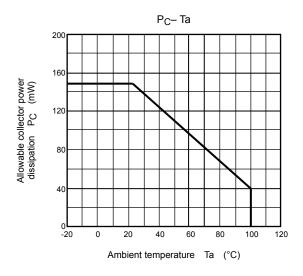
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Rise time	t <sub>r</sub>	$V_{CC}$ = 10 V, I <sub>C</sub> = 2 mA R <sub>L</sub> = 100 $\Omega$	_	2	_	
Fall time	t <sub>f</sub>		_	3	_	110
Turn-on time	t <sub>on</sub>		_	3	_	μs
Turn-off time	t <sub>off</sub>		_	3	_	
Turn-on time	t <sub>ON</sub>	$R_L$ = 1.9 k $\Omega$ (Fig.1) $R_{BE}$ = OPEN $V_{CC}$ = 5 V, I <sub>F</sub> = 16 mA	_	2	_	
Storage time	t <sub>S</sub>		_	15	_	μs
Turn-off time	t <sub>OFF</sub>		_	25	_	
Turn-on time	t <sub>ON</sub>	$R_L = 1.9 \text{ k}\Omega$ (Fig.1) $R_{BE} = 220 \text{ k}\Omega(\text{TLP631})$ $V_{CC} = 5 \text{ V}, I_F = 16 \text{ mA}$	_	2	_	
Storage time	t <sub>S</sub>		_	12	_	μs
Turn-off time	t <sub>OFF</sub>		_	20	_	

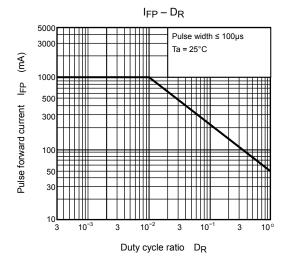
Fig. 1 Switching time test circuit

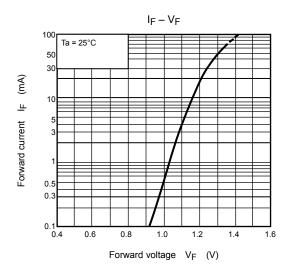


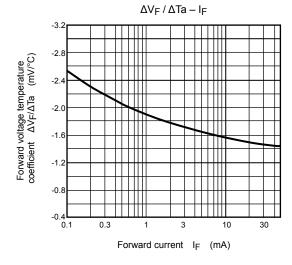


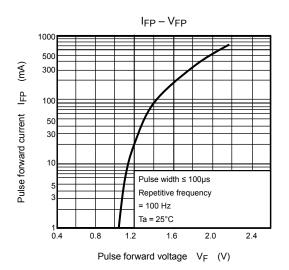


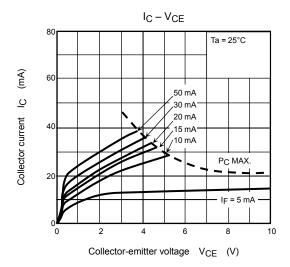


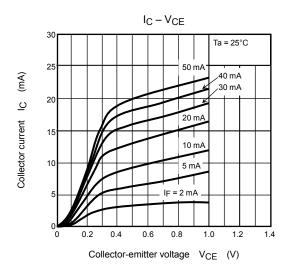


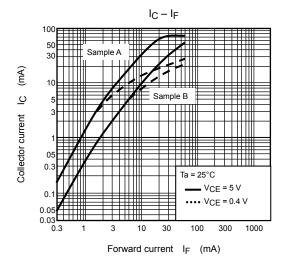


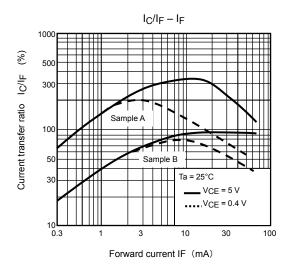


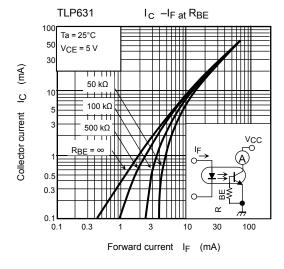


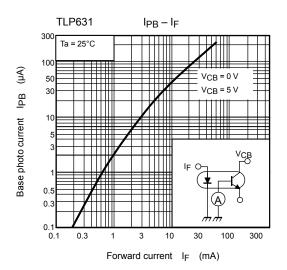


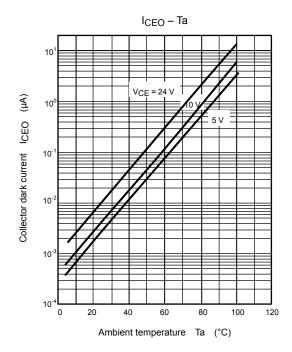


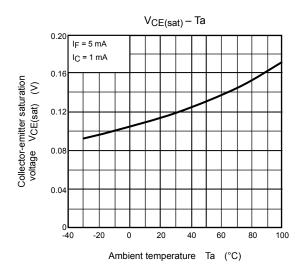


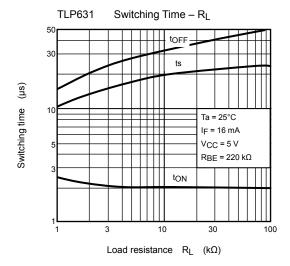


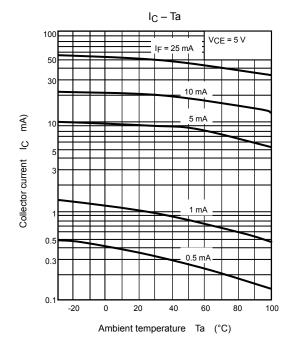


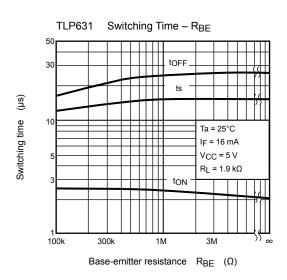












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